Small Signal MOSFET

20 V, 200 mA, Dual N-Channel, 1.0 mm x 1.0 mm SOT-963 Package

Features

- Dual N-Channel MOSFET
- Offers a Low R_{DS(ON)} Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- These are Pb-Free Devices

Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltage	V _{DSS}	20	V			
Gate-to-Source Voltag	е		V _{GS}	±8	V	
Continuous Drain	Sleady			160		
Current (Note 1)	State	T _A = 85°C	I_{D}	115	mA	
	t ≤ 5 s	$T_A = 25^{\circ}C$		200		
Power Dissipation	Steady	teady State T _A = 25°C	P _D	125		
(Note 1)	State				mW	
	t ≤ 5 s			200		
Pulsed Drain Current		t _p = 10 μs	I _{DM}	800	mA	
Operating Junction and	T _J , T _{STG}	-55 to 150	°C			
Source Current (Body D	I _S	200	mA			
Lead Temperature for S (1/8" from case for 1	TL	260	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

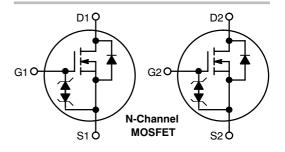
- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

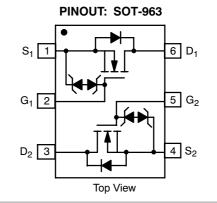


ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
	3.0 Ω @ 4.5 V	
20 V	4.0 Ω @ 2.5 V	0.2 A
	6.0 Ω @ 1.8 V	
	10 Ω @ 1.5 V	







CASE 527AA



N = Specific Device Code

M = Date Code

= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	D	1000	°C/W
Junction-to-Ambient – t = 5 s (Note 3)	$R_{ hetaJA}$	600	O/ VV

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS					-		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V
Zero Gate Voltage Drain Current		.,	T _J = 25°C			50	nA
	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = 5 \text{ V}$	T _J = 85°C			200	
		V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} =	±5.0 V			100	nA
ON CHARACTERISTICS (Note 4)	•						
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 2$	250 μA	0.4		1.0	V
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 100 \text{ M}$	100 mA		1.5	3.0	
		V _{GS} = 2.5 V, I _D = 50 mA			2.0	4.0	Ω
	R _{DS(ON)}	V _{GS} = 1.8 V, I _D = 20 mA			3.0	6.0	
		$V_{GS} = 1.5 \text{ V}, I_D = 10 \text{ mA}$ $V_{GS} = 1.2 \text{ V}, I_D = 1.0 \text{ mA}$			4.0	10	
					5.5		
Forward Transconductance	9FS	V _{DS} = 5.0 V, I _D = 125 mA			0.35		S
Source-Drain Diode Voltage	V _{SD}	V _{GS} = 0 V, I _D = 10 mA			0.6	1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE				-		
Input Capacitance	C _{ISS}				9.0		
Output Capacitance	C _{OSS}	f = 1.0 MHz, V _{GS} = 0 V V _{DS} = 15 V			3.0		pF
Reverse Transfer Capacitance	C _{RSS}	. ng – 10 t			2.2		
SWITCHING CHARACTERISTICS, V _{GS} = 4.5 V (Note 4)							
Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 200 mA,			15		
Rise Time	t _r				24		
Turn-Off Delay Time	t _{d(OFF)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 200 mA, R_{G} = 2.0 Ω			90		ns
Fall Time	t _f				60		

^{4.} Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

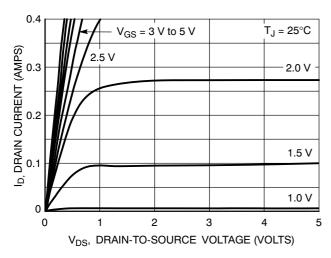


Figure 1. On-Region Characteristics

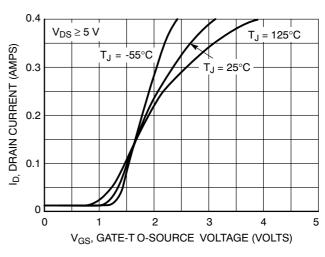


Figure 2. Transfer Characteristics

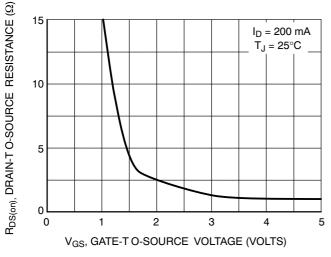


Figure 3. On-Resistance vs. Gate Voltage

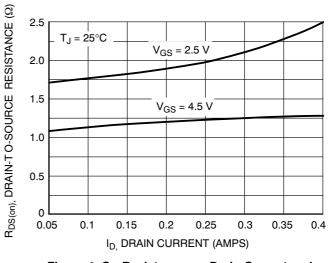


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

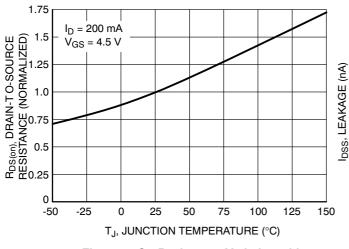


Figure 5. On-Resistance Variation with Temperature

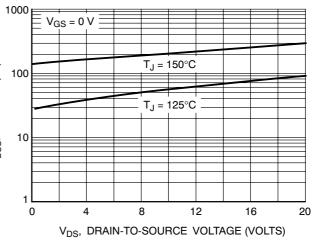


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

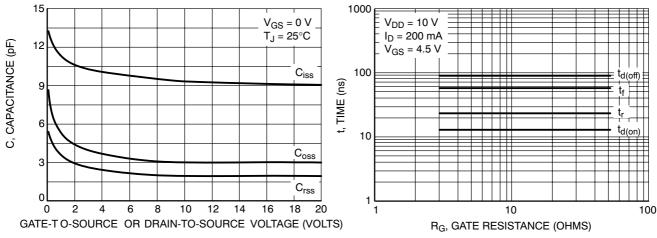


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

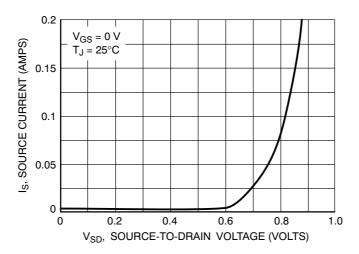


Figure 9. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Package	Shipping [†]
NTUD3128NT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

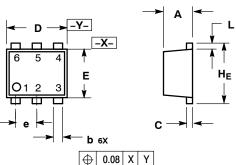
STYLE 10:

PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1



SOT-963 CASE 527AA-01 ISSUE D

DATE 30 JUL 2008



	b ex	C → ←
STYLE 1:	STYLE 2:	STYLE 3:

PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4 FMITTER 2	PIN 1. EMITTER 1 2. EMITTER2 3. BASE 2 4. COLLECTOR 2	PIN 1. CATHODE 1 2. CATHODE 1 3. ANODE/ANODE 2 4. CATHODE 2 5. CATHODE 2 6. ANODE/ANODE 1
STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE 4. ANODE 5. CATHODE 6. CATHODE	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
PIN 1. CATHODE 2. ANODE 3. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.40	0.45	0.50	0.016	0.018	0.020
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.05	0.10	0.15	0.002	0.004	0.006
D	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC		(0.014 BS	C	
L	0.05	0.10	0.15	0.002	0.004	0.006
HΕ	0.95	1.00	1.05	0.037	0.039	0.041

GENERIC MARKING DIAGRAM*

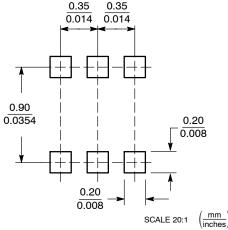


= Specific Device Code Χ

= Month Code Μ

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON18698D	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-963, 1X1, 0.35P		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales